

Data Sheet May 13, 2005 FN7430.1

Multi-Channel Buffers

The EL5129 and EL5329 integrate multiple gamma buffers and a single V_{COM} buffer for use in large panel LCD displays of 10" and greater. The EL5129 integrates 6 gamma channels and the EL5329 integrates 10 gamma channels. Half of the gamma channels in each device are designed to swing to the upper supply rail, with the other half designed to swing to the lower rail. The output capability of each channel is 10mA continuous, with 120mA peak. The gamma buffers feature a 10MHz 3dB bandwidth specification and a 9V/ μ s slew rate.

The V_{COM} amplifier is designed to swing from rail to rail. The output current capability of the V_{COM} in the EL5129 and EL5329 is 30mA continuous, 150mA peak and a slew rate of $10V/\mu s$.

Ordering Information

| PART NUMBER | PACKAGE | TAPE & REEL | PKG DWG. # | |
|------------------------------|----------------------------|-------------|------------|--|
| EL5129IRE | 20-Pin HTSSOP | - | MDP0048 | |
| EL5129IRE-T7 | 20-Pin HTSSOP | 7" | MDP0048 | |
| EL5129IRE-T13 | 20-Pin HTSSOP | 13" | MDP0048 | |
| EL5129IREZ (See Note) | 20-Pin HTSSOP (Pb-free) | - | MDP0048 | |
| EL5129IREZ-T7 (See Note) | 20-Pin HTSSOP (Pb-free) | 7" | MDP0048 | |
| EL5129IREZ-T13 (See Note) | 20-Pin HTSSOP (Pb-free) | 13" | MDP0048 | |
| EL5129IRZ (See Note) | 20-Pin TSSOP (Pb-free) | - | MDP0044 | |
| EL5129IRZ-T7 (See Note) | 20-Pin TSSOP (Pb-free) | 7" | MDP0044 | |
| EL5129IRZ-T13 (See Note) | 20-Pin TSSOP (Pb-free) | 13" | MDP0044 | |
| EL5329IREZ (See Note) | 28-Pin HTSSOP (Pb-free) | - | MDP0048 | |
| EL5329IREZ-T7 (See Note) | 28-Pin HTSSOP (Pb-free) | 7" | MDP0048 | |
| EL5329IREZ-T13 (See Note) | 28-Pin HTSSOP (Pb-free) | 13" | MDP0048 | |
| EL5329IRZ (See Note) | 28-Pin TSSOP (Pb-free) | - | MDP0044 | |
| EL5329IRZ-T7 (See Note) | 28-Pin TSSOP (Pb-free) | 7" | MDP0044 | |
| EL5329IRZ-T13 (See Note) | 28-Pin TSSOP (Pb-free) | 13" | MDP0044 | |

NOTE: Intersil Pb-free products employ special Pb-free material sets; molding compounds/die attach materials and 100% matte tin plate termination finish, which are RoHS compliant and compatible with both SnPb and Pb-free soldering operations. Intersil Pb-free products are MSL classified at Pb-free peak reflow temperatures that meet or exceed the Pb-free requirements of IPC/JEDEC J STD-020.

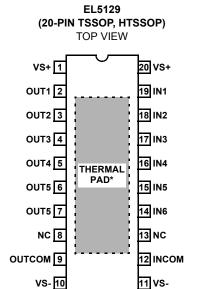
Features

- · Multiple gamma buffers
 - 6 channels (EL5129)
 - 10 channels (EL5329)
- Single V_{COM} amplifier
- · Low supply current
 - 3.5mA (EL5129)
 - 5.5mA (EL5329)
- For higher speed or higher output power, see the EL5x24 family
- · Pb-free available (RoHS compliant)

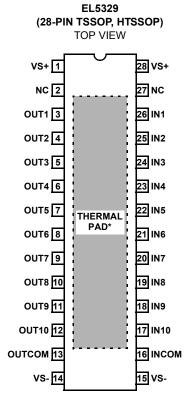
Applications

- · TFT-LCD monitors
- · LCD televisions
- · Industrial flat panel displays

Pinouts



* THERMAL PAD CONNECTED TO PIN 10 OR 11 (VS-)



* THERMAL PAD CONNECTED TO PIN 14 OR 15 (V $_{\mbox{\scriptsize S}}\mbox{-}$)

EL5129, EL5329

Absolute Maximum Ratings (T_A = 25°C)

| Supply Voltage between V _S + and V _S +18V | Power Dissipation See Curves |
|---|--|
| Input Voltage | Maximum Die Temperature |
| Maximum Continuous Output Current (VOUT0-9) 15mA | Storage Temperature |
| Maximum Continuous Output Current (V _{OUTA}) 100mA | Ambient Operating Temperature40°C to +85°C |

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

NOTE: All parameters having Min/Max specifications are guaranteed. Typ values are for information purposes only. Unless otherwise noted, all tests are at the specified temperature and are pulsed tests, therefore: $T_J = T_C = T_A$

Electrical Specifications $V_S+=+15V$, $V_{S^-}=0$, $R_L=10k\Omega$, $C_L=10pF$ to 0V, $T_A=25^{\circ}C$ unless otherwise specified

| PARAMETER | DESCRIPTION | CONDITIONS | MIN | TYP | MAX | UNIT |
|---------------------|--|--|-------|-------|--------------------------|-------|
| INPUT CHARAC | CTERISTICS (REFERENCE BUFFERS) | | | | | |
| V _{OS} | Input Offset Voltage | V _{CM} = 0V | | 2 | 20 | mV |
| TCV _{OS} | Average Offset Voltage Drift | (Note 1) | | 5 | | μV/°C |
| I _B | Input Bias Current | V _{CM} = 0V | | 2 | 50 | nA |
| R _{IN} | Input Impedance | | | 10 | | ΜΩ |
| C _{IN} | Input Capacitance | | | 1.35 | | pF |
| A _V | Voltage Gain | $1V \le V_{OUT} \le 14V$ | 0.992 | | 1.008 | V/V |
| CMIR | Input Voltage Range | EL5129, IN1 to IN3 | 1.5 | | V _S + | V |
| | | EL5329, IN1 to IN5 | 1.5 | | V _S + | V |
| | | EL5129, IN4 to IN6 | 0 | | V _S + -1.5 | V |
| | | EL5329, IN6 to IN10 | 0 | | V _S + -1.5 | V |
| INPUT CHARAC | CTERISTICS (V _{COM} BUFFER) | | | 1 | l | l . |
| V _{OS} | Input Offset Voltage | V _{CM} = 7.5V | | 1 | 20 | mV |
| TCV _{OS} | Average Offset Voltage Drift | (Note 1) | | 3 | | μV/°C |
| I _B | Input Bias Current | V _{CM} = 7.5V | | 2 | 50 | nA |
| R _{IN} | Input Impedance | | | 10 | | ΜΩ |
| C _{IN} | Input Capacitance | | | 1.35 | | pF |
| V _{REG} | Load Regulation | V _{COM} = 7.5V, -60mA < I _L < 60mA | -20 | | +20 | mV |
| CMIR _{COM} | Input Voltage Range V _{COM} | | 0 | | V _S + | V |
| OUTPUT CHAR | ACTERISTICS (REFERENCE BUFFERS) | | | | l | |
| V _{OH} | High Output Voltage - EL5129 & EL5329 (Output 1) | V _{IN} = 15V, I _O = 5mA | 14.85 | 14.9 | | V |
| | High Output Voltage - EL5129 (Output 2, 3), EL5329 (Output 2-5) | | 14.8 | 14.85 | | V |
| | High Output Voltage - EL5129 (Output 4-6), EL5329 (Output 6-10) | V _{IN} = 13.5V, I _O = 5mA | 13.45 | 13.5 | | V |
| V _{OL} | Low Output Voltage - EL5129 (Output 1-3), EL5329 (Output 1-5) | V _{IN} = 1.5V, I _O = 5mA | | 1.5 | 1.55 | V |
| | Low Output Voltage - EL5129 (Output 4-5), EL5329 (Output 6-9) | V _{IN} = 0V, I _O = 5mA | | 150 | 200 | mV |
| | Low Output Voltage - EL5129 (Output 6), EL5329 (Output 10) | | | 100 | 150 | mV |
| I _{SC} | Short Circuit Current | | 100 | 120 | | mA |

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EL5129, EL5329

$\textbf{Electrical Specifications} \qquad \text{V}_{S} + \text{= +15V}, \text{ V}_{S} - \text{= 0}, \text{ R}_{L} = \text{10k}\Omega, \text{ C}_{L} = \text{10pF to 0V}, \text{ T}_{A} = 25^{\circ}\text{C unless otherwise specified (\textbf{Continued})}$

| PARAMETER | DESCRIPTION | CONDITIONS | MIN | TYP | MAX | UNIT |
|-----------------|---|---|----------|------|------|------|
| OUTPUT CHAR | ACTERISTICS (V _{COM} BUFFER) | | | | ' | |
| V _{OH} | High Level Saturated Output Voltage | V _S + = 15V, I _O = -5mA, V _I = 15V | 14.85 | 14.9 | | V |
| V _{OL} | Low Level Saturated Output Voltage | V_S + = 15V, I_O = -5mA, V_I = 0V | | 0.1 | 0.15 | V |
| I _{SC} | Short Circuit Current | | 150 | 170 | | mA |
| POWER SUPPL | Y PERFORMANCE | | | l | | Į. |
| PSRR | Power Supply Rejection Ratio | Reference buffer V _S from 5V to 15V | 50 | 80 | | dB |
| | | V _{COM} buffer, V _S from 5V to 15V | 55 | 80 | | dB |
| Is | Total Supply Current | EL5129 | | 3.5 | 4.5 | mA |
| | | EL5329 | | 5.5 | 7 | mA |
| DYNAMIC PER | FORMANCE (BUFFER AMPLIFIERS) | | <u> </u> | l | 1 | |
| SR | Slew Rate (Note 2) | | 5 | 9 | | V/µs |
| ts | Settling to +0.1% (A _V = +1) | $(A_V = +1), V_O = 2V \text{ step}$ | | 500 | | ns |
| BW | -3dB Bandwidth | R_L = 10kΩ, C_L = 10pF | | 10 | | MHz |
| CS | Channel Separation | f = 5MHz | | 75 | | dB |
| EL5129 & EL53 | 29 DYNAMIC PERFORMANCE (V _{COM} AI | MPLIFIERS) | <u> </u> | l | 1 | |
| SR | Slew Rate (Note 2) | $-4V \le V_{OUT} \le 4V$, 20% to 80% | 7 | 10 | | V/µs |
| t _S | Settling to +0.1% (A _V = +1) | (A _V = +1), V _O = 2V step | | 350 | | ns |
| BW | -3dB Bandwidth | R _L = 10kΩ, C _L = 10pF | | 15 | | MHz |
| CS | Channel Separation | f = 5MHz | | 75 | | dB |

NOTES:

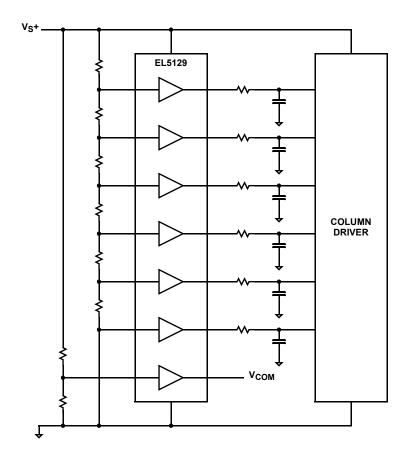
- 1. Measured over operating temperature range
- 2. Slew rate is measured on rising and falling edges

EL5129, EL5329

Pin Descriptions

| EL5129 | EL5329 | PIN NAME | PIN FUNCTION |
|--------|--------|----------|--------------------------|
| 1, 20 | 1, 28 | VS+ | Positive supply voltage |
| 2 | 3 | OUT1 | Output gamma channel 1 |
| 3 | 4 | OUT2 | Output gamma channel 2 |
| 4 | 5 | OUT3 | Output gamma channel 3 |
| 5 | 6 | OUT4 | Output gamma channel 4 |
| 6 | 7 | OUT5 | Output gamma channel 5 |
| 7 | 8 | OUT6 | Output gamma channel 6 |
| 8, 13 | 2, 27 | NC | No connect |
| 9 | 13 | OUTCOM | Output, V _{COM} |
| 10, 11 | 14, 15 | VS- | Negative supply |
| 12 | 16 | INCOM | Input, V _{COM} |
| 14 | 21 | IN6 | Input gamma channel 6 |
| 15 | 22 | IN5 | Input gamma channel 5 |
| 16 | 23 | IN4 | Input gamma channel 4 |
| 17 | 24 | IN3 | Input gamma channel 3 |
| 18 | 25 | IN2 | Input gamma channel 2 |
| 19 | 26 | IN1 | Input gamma channel 1 |
| | 9 | OUT7 | Output gamma channel 7 |
| | 10 | OUT8 | Output gamma channel 8 |
| | 11 | OUT9 | Output gamma channel 9 |
| | 12 | OUT10 | Output gamma channel 10 |
| | 17 | IN10 | Input gamma channel 10 |
| | 18 | IN9 | Input gamma channel 9 |
| | 19 | IN8 | Input gamma channel 8 |
| | 20 | IN7 | Input gamma channel 7 |

Block Diagram



Typical Performance Curves

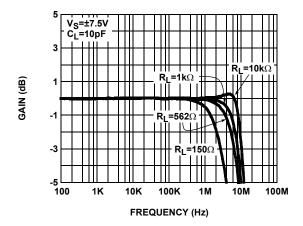


FIGURE 1. FREQUENCY RESPONSE FOR VARIOUS R_{LOAD} (BUFFER)

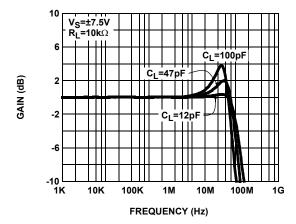


FIGURE 2. FREQUENCY RESPONSE FOR VARIOUS C_{LOAD} (BUFFER)

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Typical Performance Curves (Continued)

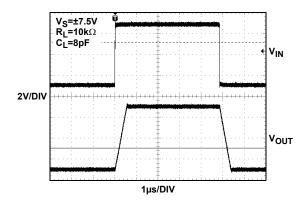


FIGURE 3. LARGE SIGNAL TRANSIENT RESPONSE (BUFFER)

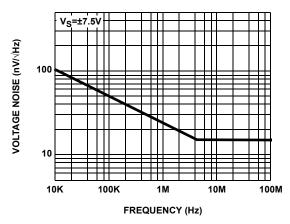


FIGURE 5. INPUT NOISE SPECIAL DENSITY vs FREQUENCY (BUFFER)

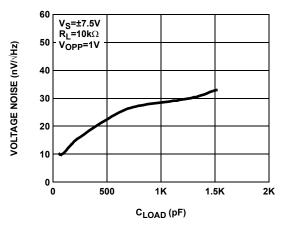


FIGURE 7. OVERSHOOT vs CAPACITANCE LOAD (BUFFER)

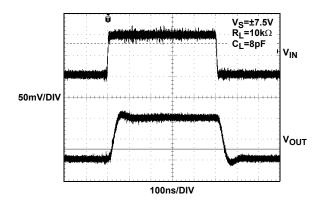


FIGURE 4. SMALL SIGNAL TRANSIENT RESPONSE (BUFFER)

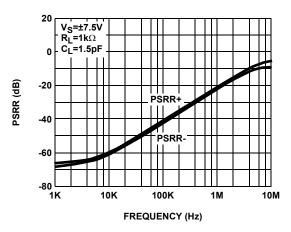


FIGURE 6. PSRR vs FREQUENCY (BUFFER)

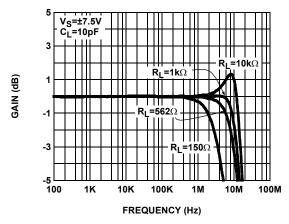


FIGURE 8. FREQUENCY RESPONSE FOR VARIOUS R_{LOAD} (V_{COM})

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Typical Performance Curves (Continued)

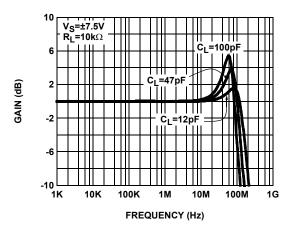


FIGURE 9. FREQUENCY RESPONSE FOR VARIOUS C_{LOAD} (V_{COM})

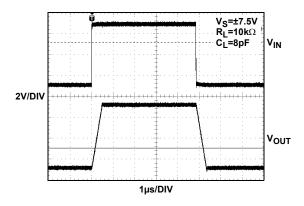


FIGURE 11. LARGE SIGNAL TRANSIENT RESPONSE (V_{COM})

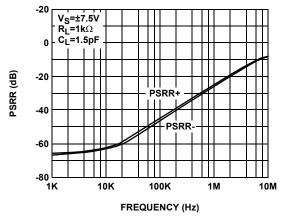


FIGURE 13. PSRR vs FREQUENCY (V_{COM})

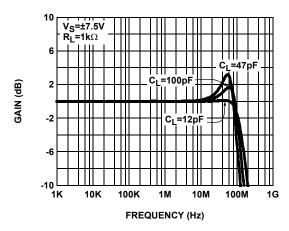


FIGURE 10. FREQUENCY RESPONSE FOR VARIOUS C_{LOAD} (V_{COM})

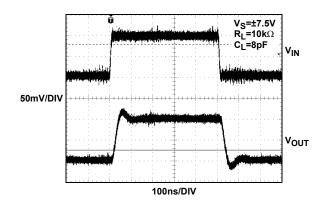


FIGURE 12. SMALL SIGNAL TRANSIENT RESPONSE (VCOM)

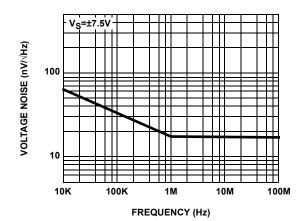


FIGURE 14. INPUT NOISE SPECIAL DENSITY vs FREQUENCY (V_{COM})

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Typical Performance Curves (Continued)

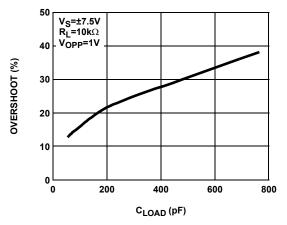


FIGURE 15. OVERSHOOT vs CAPACITANCE LOAD (VCOM)

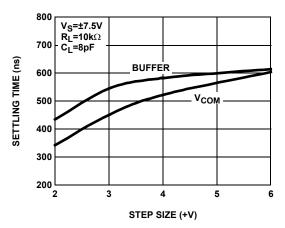


FIGURE 17. SETTLING TIME vs STEP SIZE

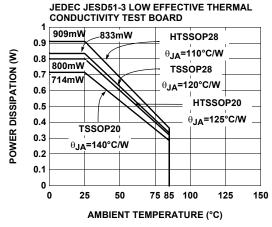


FIGURE 19. PACKAGE POWER DISSIPATION VS AMBIENT TEMPERATURE

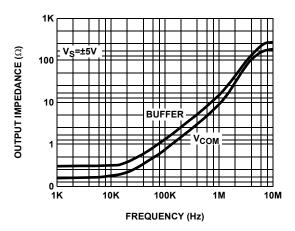


FIGURE 16. OUTPUT IMPEDANCE vs FREQUENCY

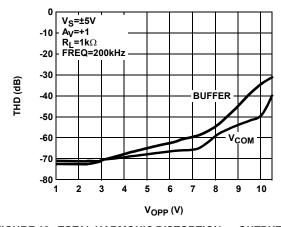


FIGURE 18. TOTAL HARMONIC DISTORTION vs OUTPUT VOLTAGE

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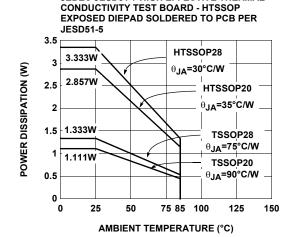


FIGURE 20. PACKAGE POWER DISSIPATION VS AMBIENT TEMPERATURE

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Description of Operation and Application Information

Product Description

The EL5129 and EL5329 are fabricated using a high voltage CMOS process. They exhibit rail to rail input and output capability and have very low power consumption. When driving a load of 10K and 12pF, the buffers have a -3dB bandwidth of 10MHz and exhibit 9V/ μ s slew rate. The VCOM amplifier has a -3dB bandwidth of 12MHz and exhibit 10V/ μ s slew rate.

Input, Output, and Supply Voltage Range

The EL5129 and EL5329 are specified with a single nominal supply voltage from 5V to 15V or a split supply with its total range from 5V to 15V. Correct operation is guaranteed for a supply range from 4.5V to 16.5V.

The input common-mode voltage range of the EL5129 and EL5329 within 500mV beyond the supply rails. The output swings of the buffers and V_{COM} amplifier typically extend to within 100mV of the positive and negative supply rails with load currents of 5mA. Decreasing load currents will extend the output voltage even closer to each supply rails.

Output Phase Reversal

The EL5129 and EL5329 are immune to phase reversal as long as the input voltage is limited from V_{S^-} -0.5V to V_{S^+} +0.5V. Although the device's output will not change phase, the input's over-voltage should be avoided. If an input voltage exceeds supply voltage by more than 0.6V, electrostatic protection diode placed in the input stage of the device begin to conduct and over-voltage damage could occur.

Output Drive Capability

The EL5129 and EL5329 do not have internal short-circuit protection circuitry. The buffers will limit the short circuit current to $\pm 120 \text{mA}$ and the V_{COM} amplifier will limit the short circuit current to $\pm 170 \text{mA}$ if the outputs are directly shorted to the positive or the negative supply. If the output is shorted indefinitely, the power dissipation could easily increase such that the part will be destroyed. Maximum reliability is maintained if the output continuous current never exceeds $\pm 15 \text{mA}$ for the buffers and $\pm 100 \text{mA}$ for the V_{COM} amplifier. These limits are set by the design of the internal metal interconnections.

The Unused Buffers

It is recommended that any unused buffers should have their inputs tied to ground plane.

Power Dissipation

With the high-output drive capability of the EL5129 and EL5329, it is possible to exceed the 125°C "absolute-maximum junction temperature" under certain load current conditions. Therefore, it is important to calculate the

maximum junction temperature for the application to determine if load conditions need to be modified for the buffer to remain in the safe operating area.

The maximum power dissipation allowed in a package is determined according to:

$$\mathsf{P}_{\mathsf{DMAX}} = \frac{\mathsf{T}_{\mathsf{JMAX}} - \mathsf{T}_{\mathsf{AMAX}}}{\Theta_{\mathsf{JA}}}$$

where:

- T_{JMAX} = Maximum junction temperature
- T_{AMAX} = Maximum ambient temperature
- $\theta_{\text{.IA}}$ = Thermal resistance of the package
- P_{DMAX} = Maximum power dissipation in the package

The maximum power dissipation actually produced by an IC is the total quiescent supply current times the total power supply voltage, plus the power in the IC due to the loads, or:

$$\begin{array}{l} P_{DMAX} = V_S \times I_S + \Sigma i \times [(V_S + -V_{OUT} i) \times I_{LOAD} i] + \\ (V_S + -V_{OUT}) \times I_{LA} \end{array}$$

when sourcing, and:

$$\begin{array}{l} P_{DMAX} = V_S \times I_S + \Sigma i \times [(V_{OUT}i - V_S \text{-}) \times I_{LOAD}i] + \\ (V_{OUT} - V_S \text{-}) \times I_{LA} \end{array}$$

when sinking.

where:

- i = 1 to total number of buffers
- V_S = Total supply voltage of buffer and V_{COM}
- I_{SMAX} = Total quiescent current
- V_{OUT}i = Maximum output voltage of the application
- V_{OUT} = Maximum output voltage of V_{COM}
- I_{I OAD}i = Load current of buffer
- I_{LA} = Load current of V_{COM}

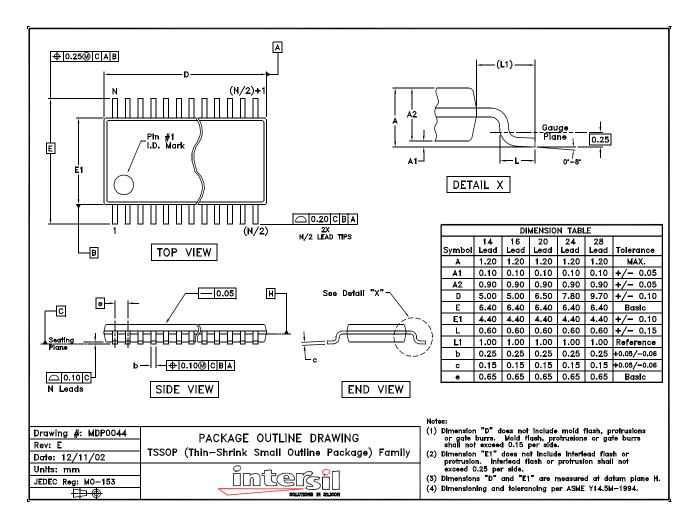
If we set the two P_{DMAX} equations equal to each other, we can solve for the R_{LOAD} 's to avoid device overheat. The package power dissipation curves provide a convenient way to see if the device will overheat. The maximum safe power dissipation can be found graphically, based on the package type and the ambient temperature. By using the previous equation, it is a simple matter to see if P_{DMAX} exceeds the device's power derating curves.

Power Supply Bypassing and Printed Circuit Board Layout

As with any high frequency device, good printed circuit board layout is necessary for optimum performance. Ground plane construction is highly recommended, lead lengths should be as short as possible, and the power supply pins must be well bypassed to reduce the risk of oscillation. For normal single supply operation, where the V_S- pin is connected to ground, one 0.1µF ceramic capacitor should be placed from the V_S+ pin to ground. A 4.7µF tantalum capacitor should then be connected from the V_S+ pin to ground. One 4.7µF capacitor may be used for multiple devices. This same capacitor combination should be placed at each supply pin to ground if split supplies are to be used.

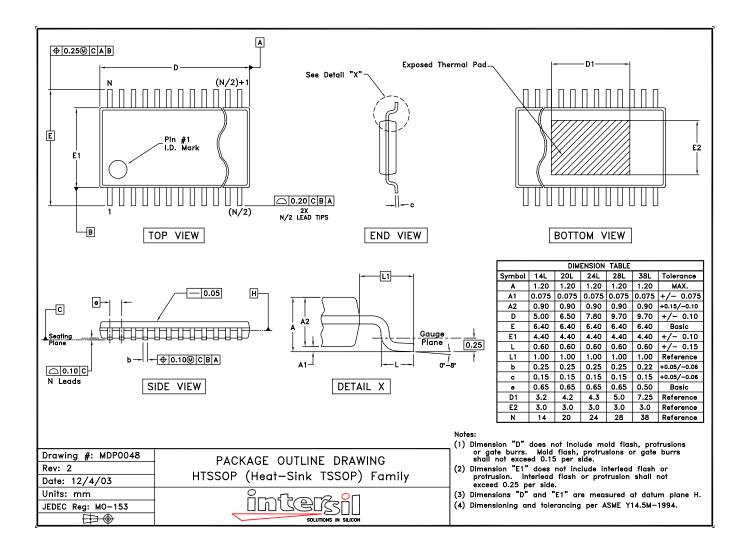
Important Note: The metal plane used for heat sinking of the device is electrically connected to the negative supply potential (V_{S^-}). If V_{S^-} is tied to ground, the thermal pad can be connected to ground. Otherwise, the thermal pad must be isolated from any other power planes.

TSSOP Package Outline Drawing



in<u>ter</u>sil

HTSSOP Package Outline Drawing



NOTE: The package drawing shown here may not be the latest version. To check the latest revision, please refer to the Intersil website at http://www.intersil.com/design/packages/index.asp

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